NIKO-SEM

Dual N-Channel Enhancement Mode Field Effect Transistor

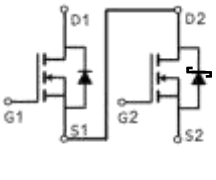
PK626HY

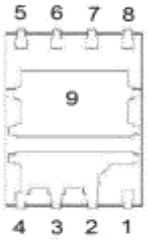
PDFN 5x6P

Halogen-Free & Lead-Free

PRODUCT SUMMARY

	$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
Q2	30V	2.4mΩ	99A
Q1	30V	7mΩ	43A





1 : G1
2,3,4 : D1
5,6,7 : S2
8 : G2
9 : S1/D2

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	Q2	Q1	UNITS
Drain-Source Voltage		V_{DS}	30	30	V
Gate-Source Voltage		V_{GS}	±20	±20	V
Continuous Drain Current[3]	T_C = 25 °C	I_D	99	43	A
	T_C = 100 °C		63	27	
Pulsed Drain Current[1]		I_{DM}	120	55	
Continuous Drain Current	T_A = 25 °C	I_D	25	11	
	T_A = 70 °C		20	9.5	
Avalanche Current		I_{AS}	48	23	
Avalanche Energy	L = 0.1mH	E_{AS}	115	26.4	mJ
Power Dissipation	T_C = 25 °C	P_D	43	24	W
	T_C = 100 °C		17	9.6	
Power Dissipation	T_A = 25 °C	P_D	2.7	1.7	W
	T_A = 70 °C		1.7	1.1	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL		TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient[2]	$R_{\theta JA}$	Q2		46	°C / W
	$R_{\theta JA}$	Q1		70	
Junction-to-Case	$R_{\theta JC}$	Q2		2.9	
	$R_{\theta JC}$	Q1		5.2	

[1]Pulse width limited by maximum junction temperature $T_{J(MAX)}$=150°C.
[2]The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any given application depends on the user's specific board design.
[3]Package limitation current :Q1=29A,Q2=34A

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

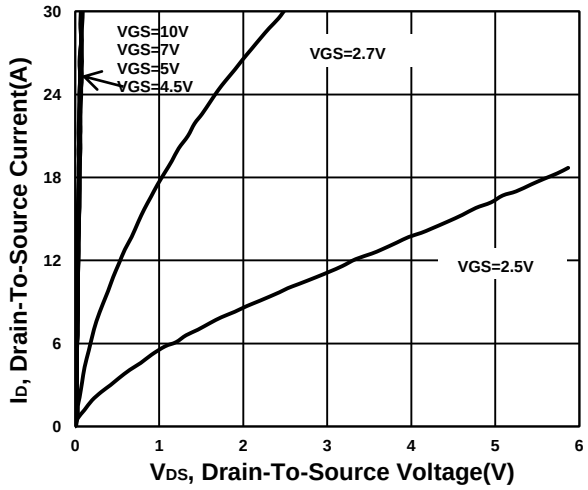
PARAMETER	SYMBOL	TEST CONDITIONS		LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	Q2	30			V
		V_{GS} = 0V, I_D = 250μA	Q1	30			
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	Q2	1.3	1.75	2.3	
			Q1	1.3	1.75	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	Q2			±100	nA
			Q1			±100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24V, V_{GS} = 0V	Q2			0.5	mA
			Q1			1	μA
		V_{DS} = 20V, V_{GS} = 0V, T_J = 55 °C	Q2			5	mA
			Q1			10	μA
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} =4.5V, I_D = 15A	Q2		2.3	3	mΩ
		V_{GS} =4.5V, I_D = 11A	Q1		7.4	9.5	
		V_{GS} = 10V, I_D = 20A	Q2		1.9	2.4	
		V_{GS} = 10V, I_D = 11A	Q1		5.6	7	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A	Q2		70		S
		V_{DS} = 5V, I_D = 11A	Q1		50		
DYNAMIC							
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 15V, f = 1MHz	Q2		3232		pF
			Q1		824		
Output Capacitance	C_{oss}		Q2		606		
			Q1		162		
Reverse Transfer Capacitance	C_{rss}		Q2		353		
			Q1		103		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz	Q2		1.25		Ω
			Q1		2.3		
Total Gate Charge[2]	Q_g VGS = 10V	Q2 V_{DS} = 15V , V_{GS} = 10V, I_D = 20A Q1 V_{DS} = 15V , V_{GS} = 10V, I_D = 11A	Q2		63		nC
			Q1		18		
	Q_g VGS = 4.5V		Q2		34		
			Q1		10		
Gate-Source Charge[2]	Q_{gs}		Q2		8.3		
			Q1		2		
Gate-Drain Charge[2]	Q_{gd}		Q2		15.5		
			Q1		6		

Turn-On Delay Time[2]	$t_{d(on)}$	Q2 V_{DS} = 15V , $I_D \cong$ 20A, V_{GS} = 10V, R_{GEN} =6Ω Q1 V_{DS} = 15V , $I_D \cong$ 11A, V_{GS} = 10V, R_{GEN} =6Ω	Q2		31		nS
			Q1		27		
Rise Time[2]	t_r		Q2		15		
			Q1		20		
Turn-Off Delay Time[2]	$t_{d(off)}$		Q2		64		
			Q1		40		
Fall Time[2]	t_f		Q2		22		
			Q1		19		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)							
Continuous Current[3]	I_S		Q2			71	A
			Q1			20	
Forward Voltage[1]	V_{SD}	I_F = 1A, V_{GS} = 0V	Q2			0.6	V
		I_F = 11A, V_{GS} = 0V	Q1			1.2	
Reverse Recovery Time	t_{rr}	Q2 I_F = 20A, dI_F/dt = 100A / μS Q1 I_F = 11A, dI_F/dt = 100A / μS	Q2		28.8		nS
			Q1		16.5		
Reverse Recovery Charge	Q_{rr}		Q2		12.7		nC
			Q1		5.2		

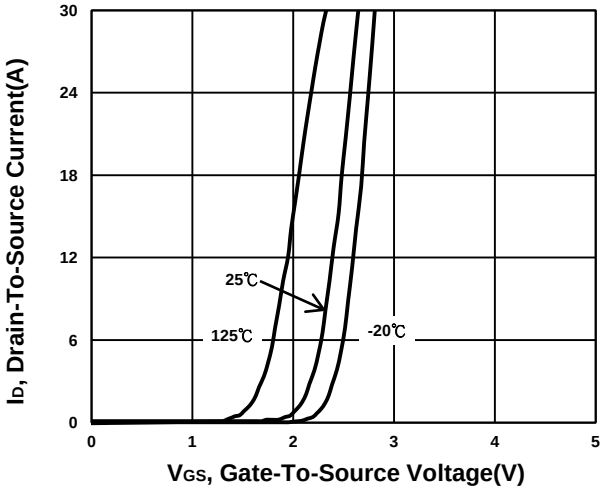
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.
[3]Package limitation current :Q1=29A,Q2=34A

TYPICAL PERFORMANCE CHARACTERISTICS
Q2

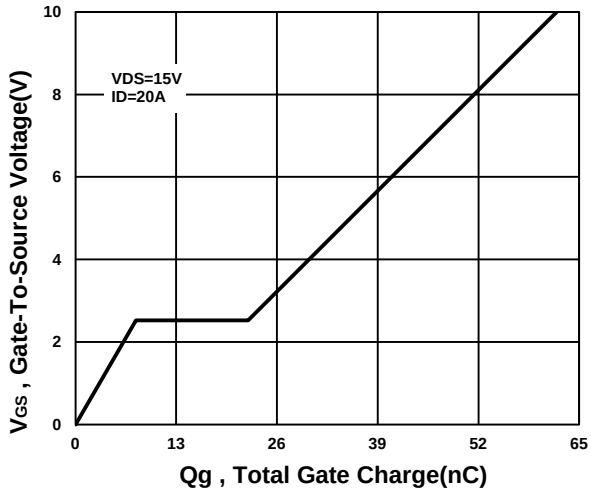
Output Characteristics



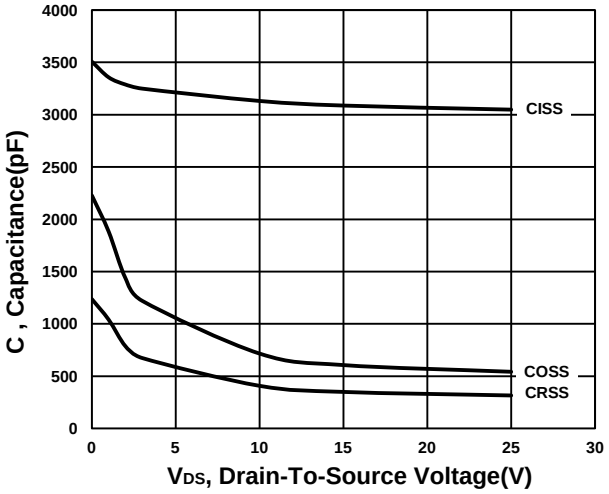
Transfer Characteristics



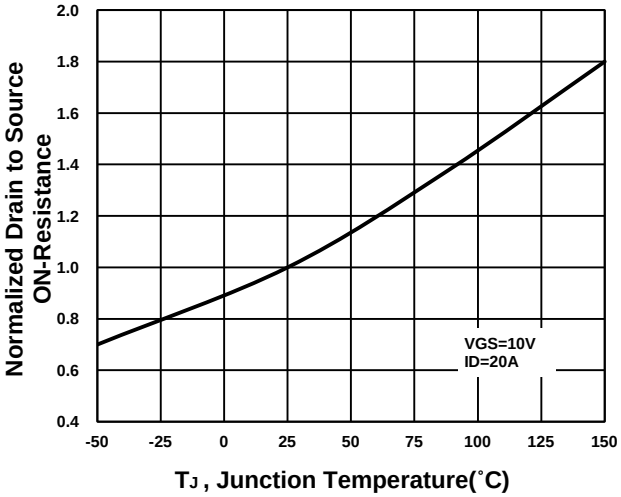
Gate charge Characteristics



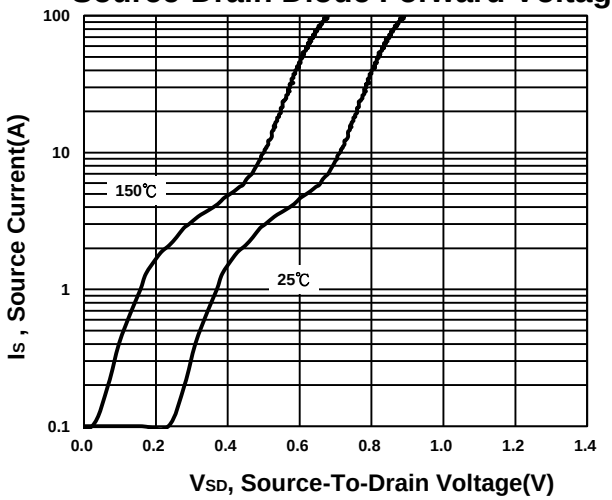
Capacitance Characteristic



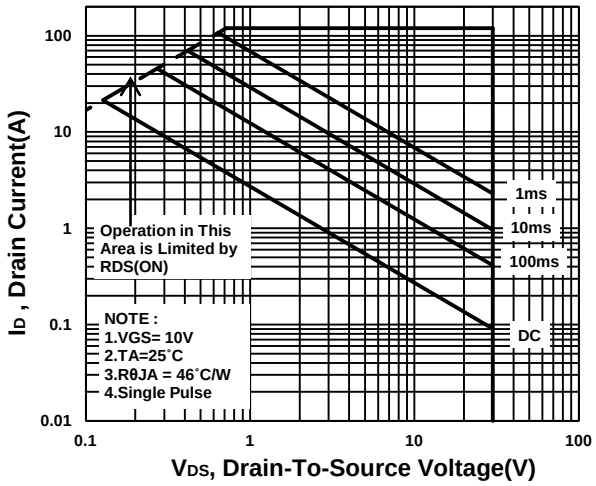
On-Resistance VS Temperature



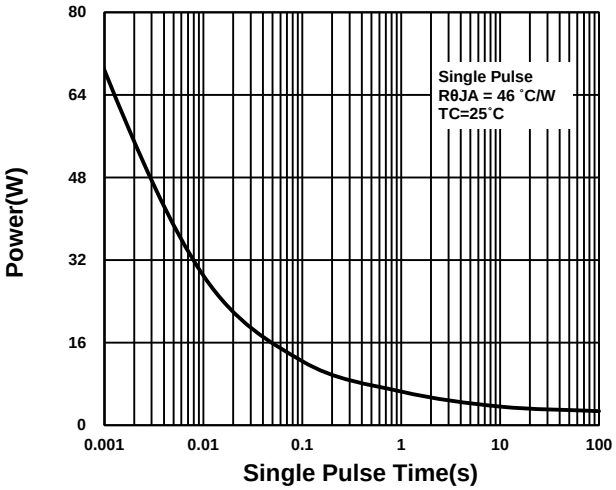
Source-Drain Diode Forward Voltage



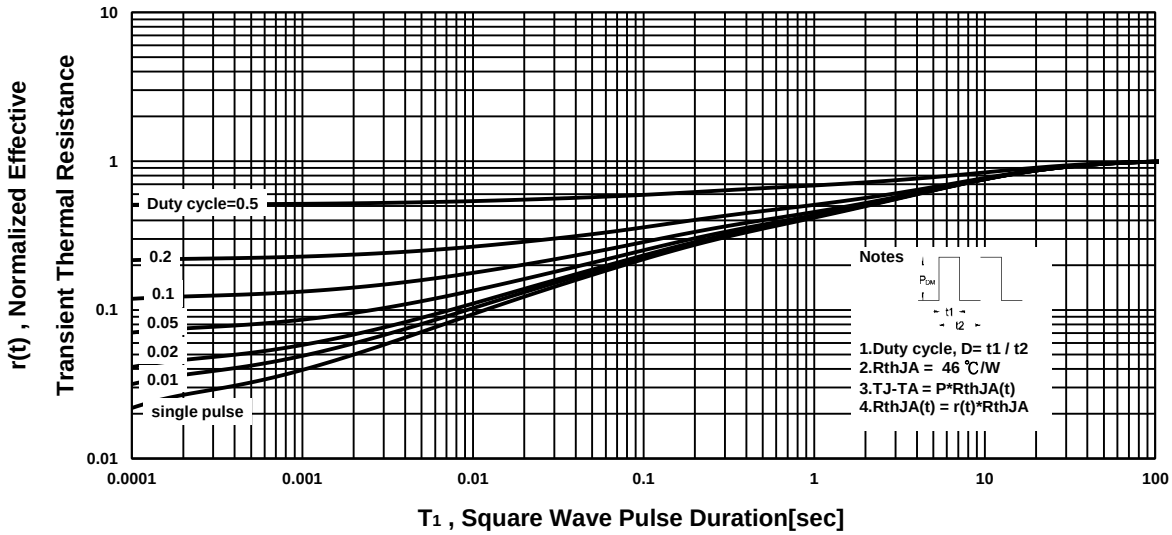
Safe Operating Area



Single Pulse Maximum Power Dissipation

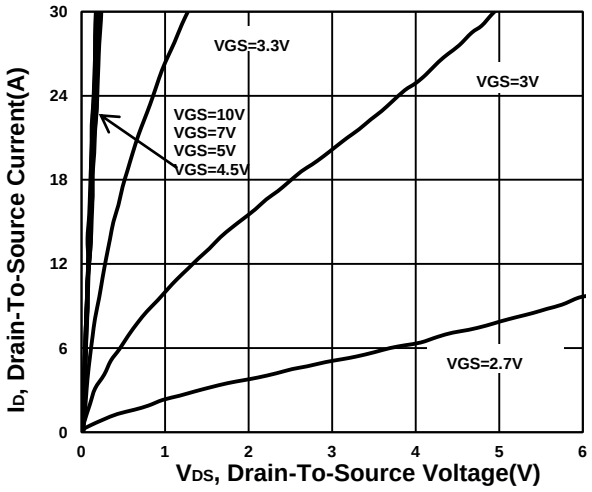


Transient Thermal Response Curve

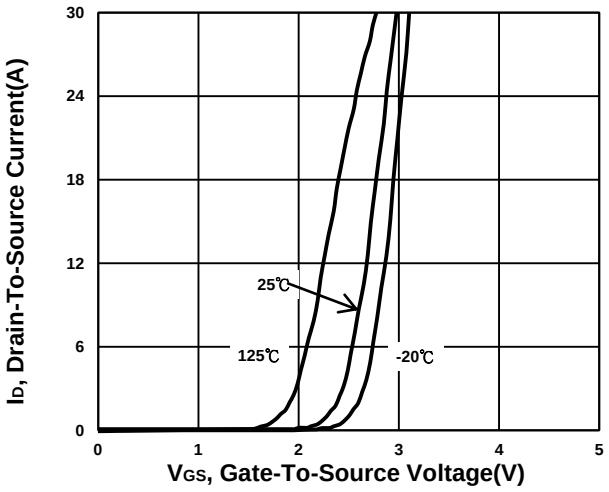


Q1

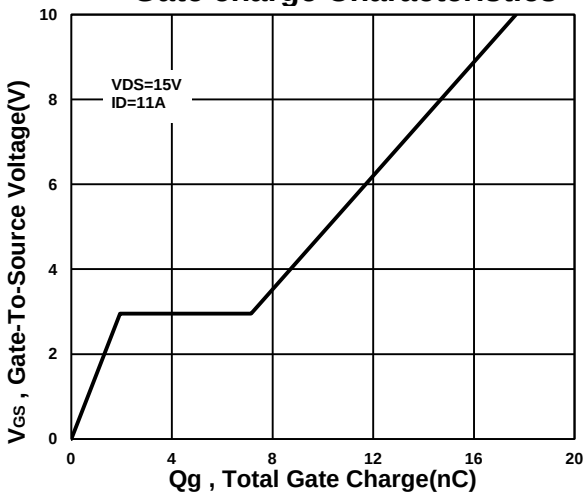
Output Characteristics



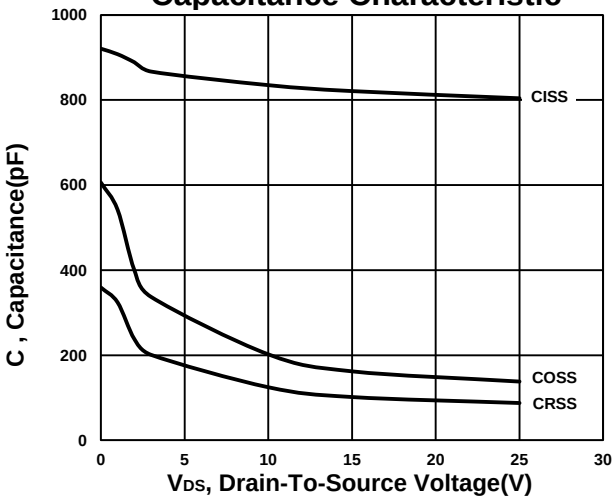
Transfer Characteristics



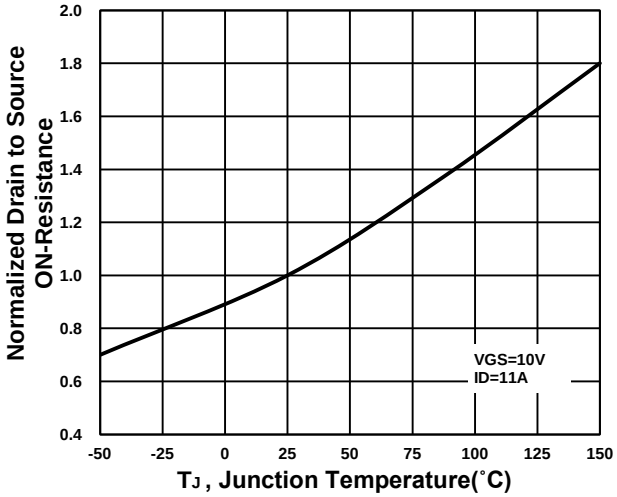
Gate charge Characteristics



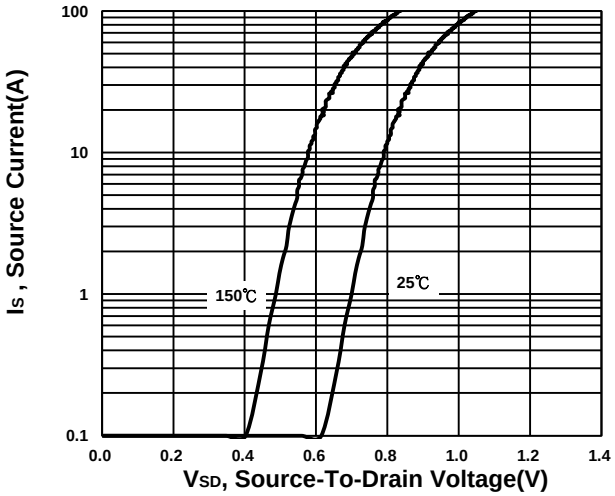
Capacitance Characteristic



On-Resistance VS Temperature



Source-Drain Diode Forward Voltage



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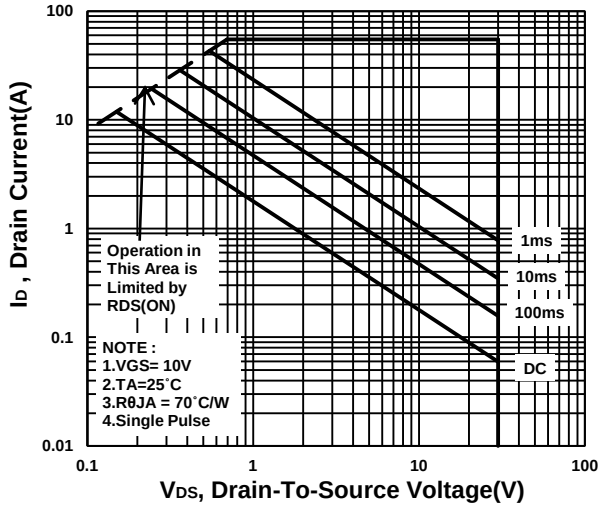

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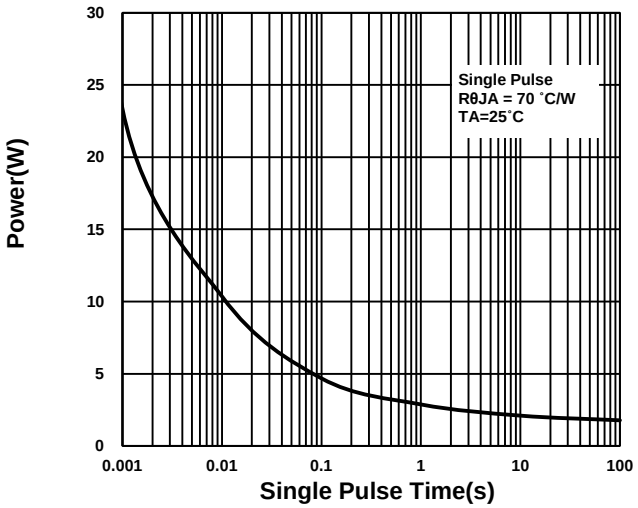

Transient Thermal Response Curve